

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

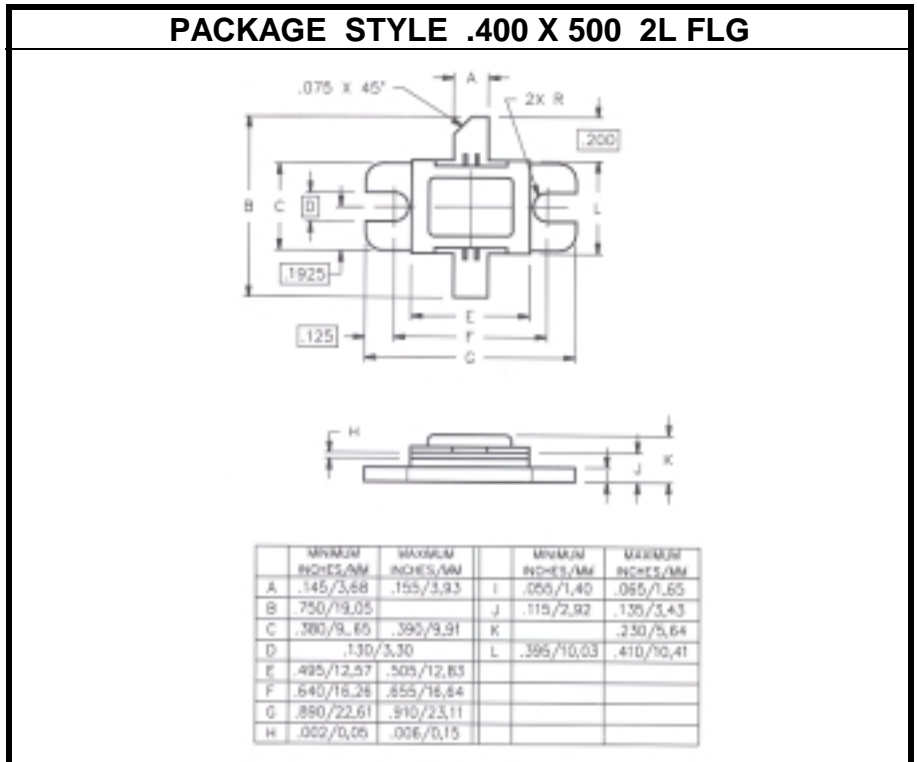
The **ASI SD1542** is a Common Base Device Designed for, IFF and DME Pulse Applications.

FEATURES INCLUDE:

- Gold Metalization
- Input/Output Matching
- Hermetically Sealed

MAXIMUM RATINGS

I_C	40 A
V_{CES}	65 V
V_{CBO}	65 V
P_{DISS}	1350 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.06 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 25 mA	65			V
BV_{CES}	I _C = 50 mA	65			V
BV_{EBO}	I _E = 10 mA	3.5			V
I_{CES}	V _{CE} = 50 V			35	mA
h_{FE}	V _{CE} = 5.0 V I _C = 250 mA	5.0		200	---
P_G	V _{CC} = 50 V P _{IN} = 150 W f = 1025 to 1150 MHz	5.6			dB
P_{OUT}	PULSE WIDTH = 10 μS DUTY CYCLE = 1.0%	550			W